

250 mW Linear Power Amplifier and T/R Switch

1.8 - 2.0 GHz

AM55-0004

Features

- Operates Over Full PCN/PCS/PHS Bands
- Operates Over +3 V to +5 V Supply Voltage
- +24 dBm P_{1dB} Typical at PA Out
- 35% PAE @ P_{1dB} for Linear Operation
- On-Chip T/R Switch, Linear Operation to +30 dBm
- Low Cost SSOP-28 Plastic Package

Description

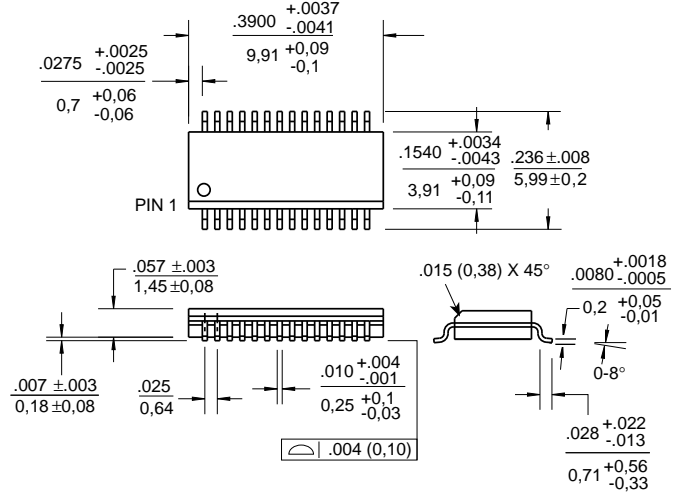
M/A-COM's AM55-0004 power amplifier/switch integrates a power amplifier and transmit/receive switch in a low cost SSOP package. The power amplifier delivers +24 dBm of linear power with high efficiency and can be operated at supply voltages as low as 2.7 V. It is ideally suited for QPSK or other linearly modulated systems in the 1.8 to 2.0 GHz frequency band.

The power amplifier/switch is fully monolithic and requires only one output capacitor for power match. The T/R switch achieves good insertion loss and isolation without degrading the overall linearity.

The AM55-0004 is ideally suited for final stage power amplification in linear TDD systems. The integrated switch is convenient for duplexing. The AM55-0004 can also be used as a driver stage for high power systems. Typical applications include Japanese PHS systems or PCN/PCS transmit chains.

M/A-COM's AM55-0004 is fabricated using a mature 0.5-micron gate length GaAs process. The process features full passivation for increased performance and reliability.

SSOP-28



Dimensions are inches over millimeters.

Ordering Information

Part Number	Description
AM55-0004	SSOP 28-Lead Plastic Package
AM55-0004TR	Forward Tape & Reel*
AM55-0004RTR	Reverse Tape & Reel*
AM55-0004SMB	Designer's Kit

* If specific reel size is required, consult factory for part number assignment.

Typical Electrical Specifications

Test conditions: Frequency: 1.9 GHz, V_{DD1} = V_{DD2} = 4.8 V ±10%, V_{G1} adjusted for 30 mA quiescent bias on V_{DD1}, V_{G2} adjusted for 65 mA quiescent bias on V_{DD2}, T_A = +25°C

Parameter	Units	Min.	Typ.	Max.
Power Amplifier				
Linear Gain	dB	22	24	
Power Output @ P _{1dB} at PA OUT port	dBm	22.5	24	
Current From Positive Supply @ P _{1dB}	mA	75	175	275
Input VSWR			2.0:1	
T/R Switch				
Insertion Loss	dB		0.6	1.0
Input Match			1.5:1	
Isolation	dB	15	20	

Absolute Maximum Ratings¹

Parameter	Absolute Maximum
Max. Input Power ²	+23 dBm
Operating Voltages ²	$V_{DD} = 7\text{ V}$
	$V_{GG} = -5\text{ V}$
	$V_{DD} - V_{GG} = 8\text{ V}$
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

1. Exceeding these limits may cause permanent damage.
2. Ambient temperature (T_A) = +25°C

Pin Configuration

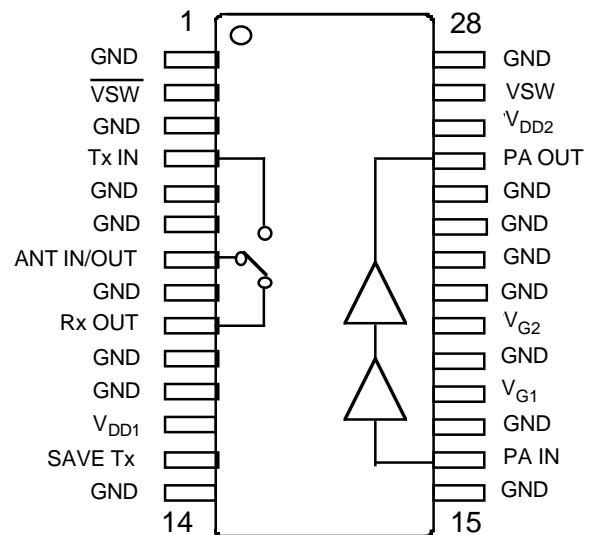
Pin No.	Pin Name	Description
1	GND	DC and RF Ground
2	\overline{VSW}	Complimentary T/R Switch Control, -4 V Tx mode/0 V Rx mode
3	GND	DC and RF Ground
4	Tx IN	Transmit side of T/R switch
5	GND	DC and RF Ground
6	GND	DC and RF Ground
7	ANT IN/OUT	Common port of T/R switch which is connected to the antenna
8	GND	DC and RF Ground
9	Rx OUT	Receive side of T/R switch
10	GND	DC and RF Ground
11	GND	DC and RF Ground
12	V_{DD1}	Positive bias for the first stage of PA, +2.7 to +6.0 volts
13	SAVE Tx	Sleep mode control of first stage of PA ONLY 0 V — first PA stage on -4 V — first PA stage off
14	GND	DC and RF Ground
15	GND	DC and RF Ground
16	PA IN	RF input of the Power Amplifier
17	GND	DC and RF Ground
18	V_{G1}	Negative bias control for the first PA stage, voltage divider is on the MMIC, adjusted to set V_{DD1} quiescent bias current, which is typically 30 mA. Input impedance: 10 k Ω
19	GND	DC and RF Ground
20	V_{G2}	Negative bias control for the second PA stage, adjusted to set V_{DD2} quiescent bias current, which is typically 65 mA. Input impedance: > 1M Ω
21	GND	Second Stage DC and RF Ground
22	GND	Second Stage DC and RF Ground
23	GND	Second Stage DC and RF Ground
24	GND	Second Stage DC and RF Ground
25	PA OUT	RF output of the Power Amplifier
26	V_{DD2}	Positive bias for the second stage of the PA, +2.7 to +6.0 volts
27	VSW	T/R Switch Control, 0 V Tx mode/-4 V Rx mode
28	GND	DC and RF Ground

Truth Table

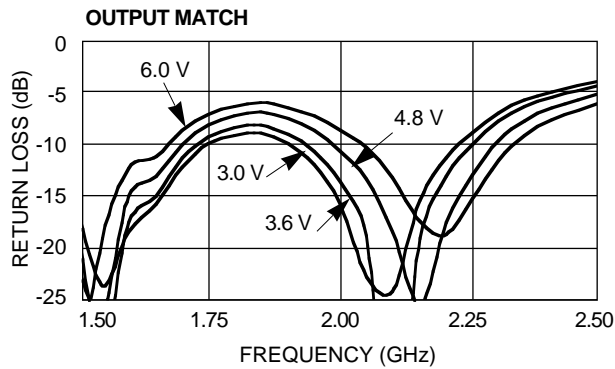
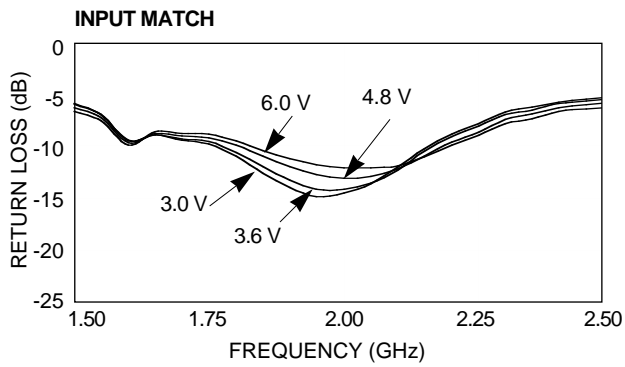
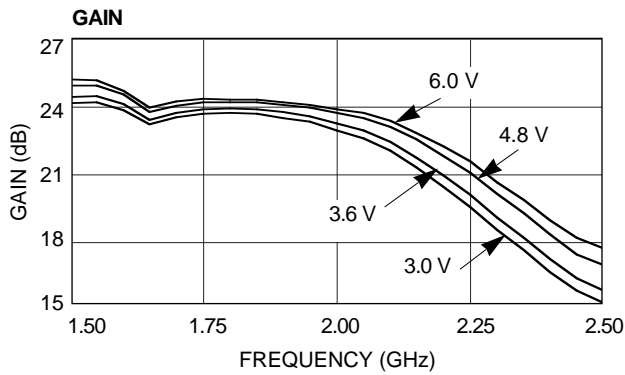
Operating Mode	VSW	\overline{VSW}	SAVE Tx
PA Tx	X	X	0 V
PA Sleep	X	X	-4.0 Volts
T/R Switch Tx	0 Volts	-4.0 Volts	X
T/R Switch Rx	-4.0 Volts	0 Volts	X

X - Don't Care

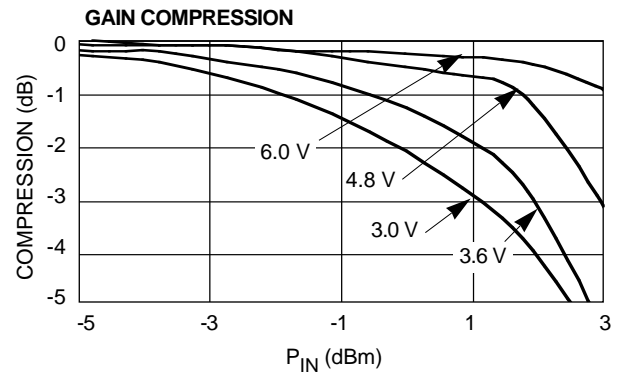
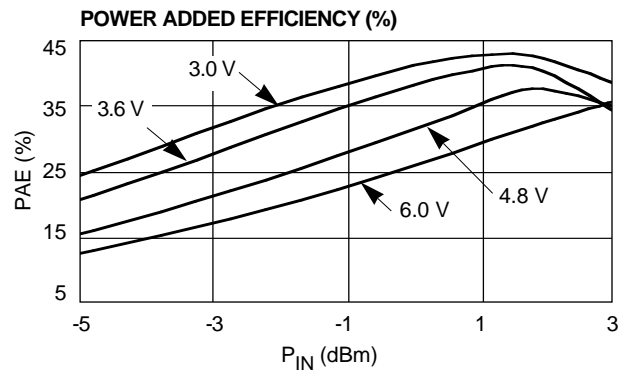
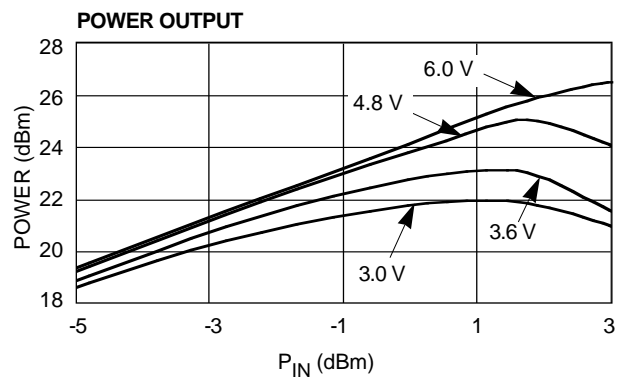
Functional Diagram and Pin Configuration



Power Amplifier Small Signal Performance¹

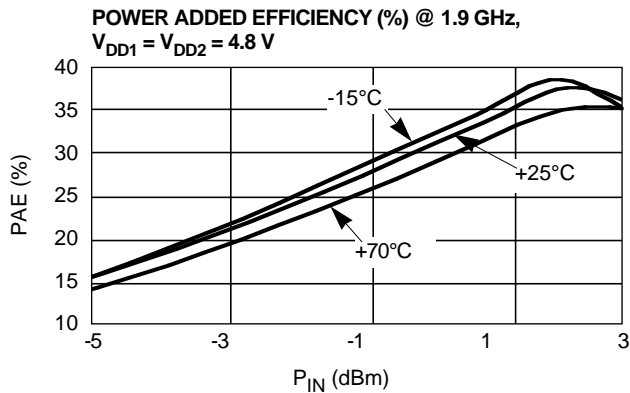
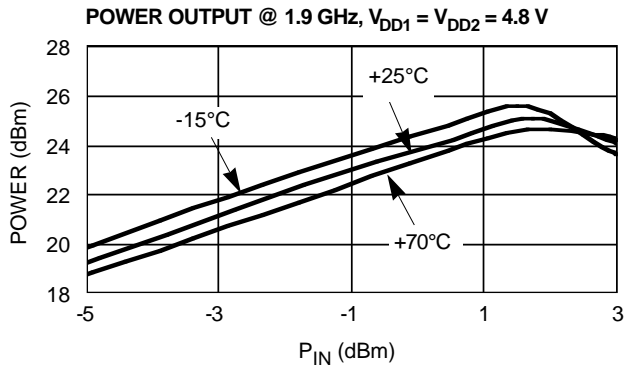
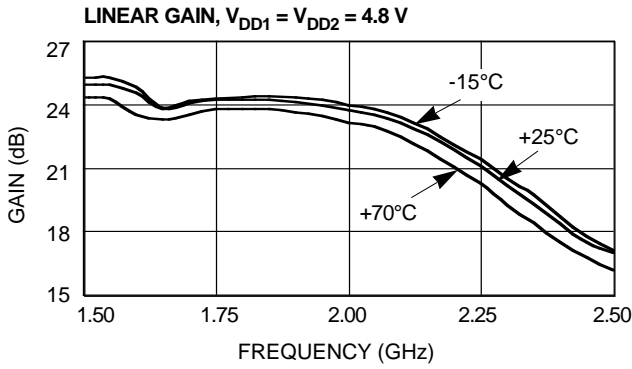


Power Amplifier CW Performance at 1.9 GHz¹

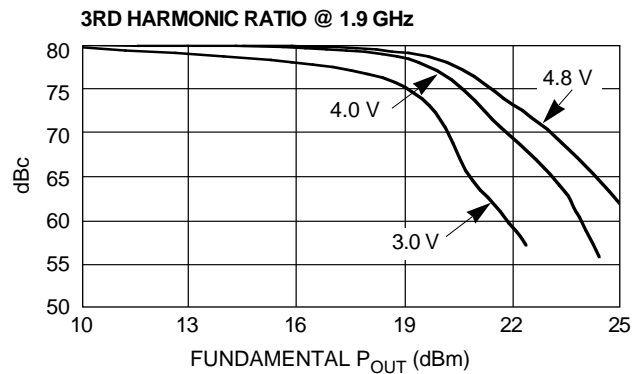
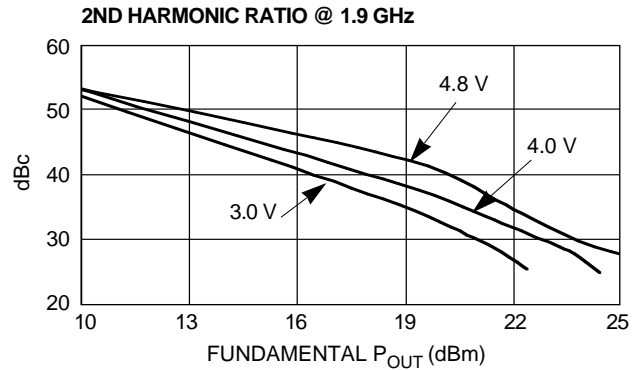
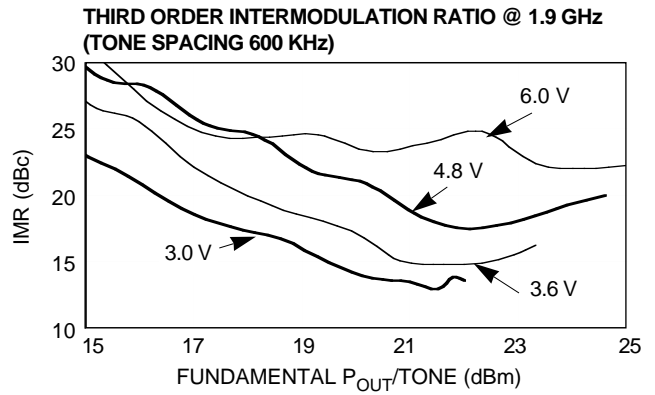


1. All data measured at $T_A = +25^\circ\text{C}$ and V_{G1} , V_{G2} adjusted for first stage quiescent current of 30 mA and second stage current of 65 mA, respectively.

Power Amplifier Temperature Performance¹



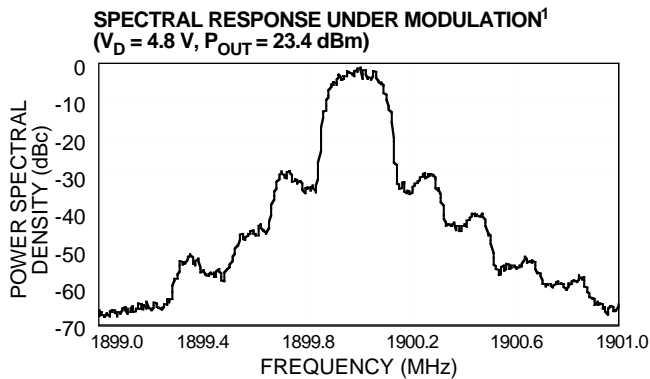
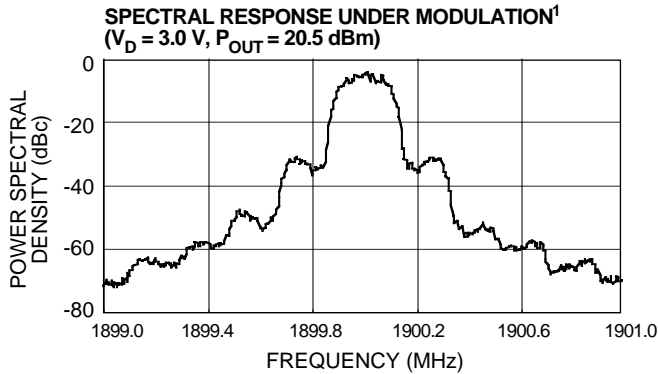
Power Amplifier Spurious Response at Various Supply Voltages¹



1. All data measured at $T_A = +25^\circ\text{C}$ and V_{G1} , V_{G2} adjusted for first stage quiescent current of 30 mA and second stage current of 65 mA, respectively.

Power Amplifier Spectral Response Under Modulation Drive

($\pi/4$ DQPSK, $\alpha = 0.5$, 384 kB/sec, 9-bit PN code)

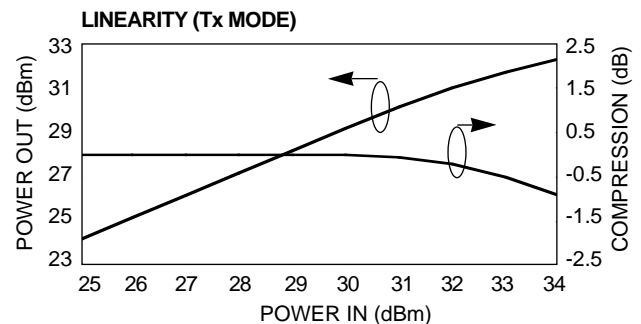
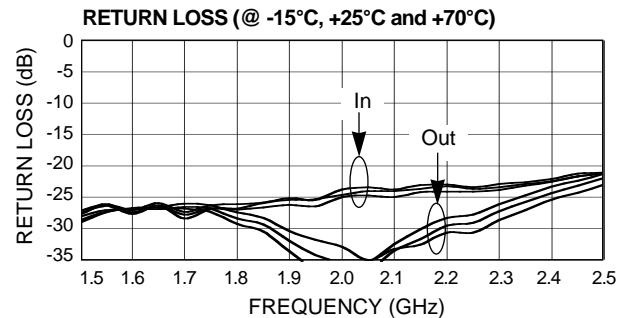
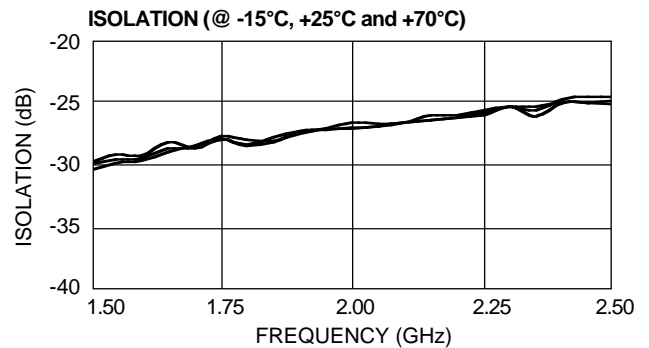
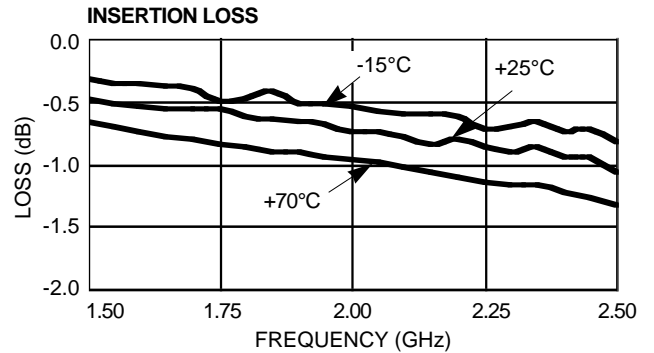


Output Power Under Modulation²

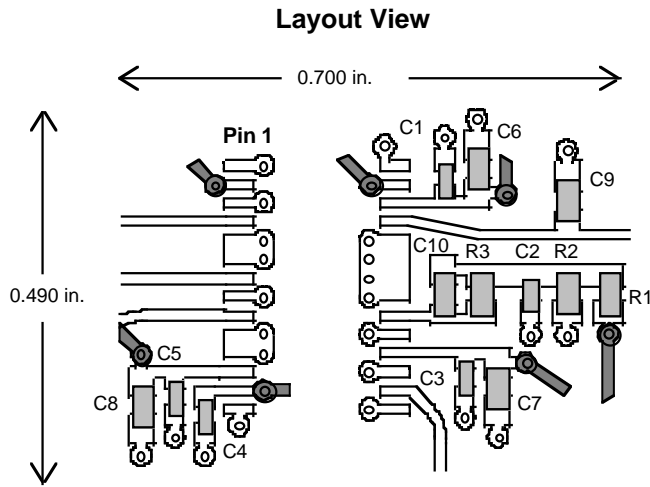
V_D (volts)	P_{OUT} (dBm)
3	20.5
3.6	21.4
4	22.2
4.8	23.4
6	23.7

- Spectral output is tested under the following conditions:
 Modulation scheme is $\pi/4$ DQPSK with a bit transfer rate of 384 kB/sec and a root Nyquist filter with $\alpha = 0.5$ per RCR STD-28. The spectrum analyzer settings are as follows:
 Resolution bandwidth: 10 kHz
 Video bandwidth: 100 kHz
 Sweep time: 5 seconds
- This chart documents the modulated output power delivered for a fixed adjacent channel interference (ACI) rejection of 55 dBc at a 600-kHz offset.

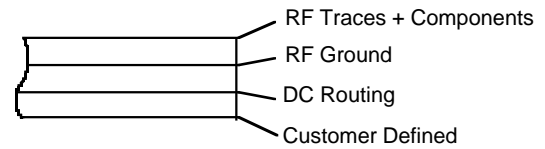
Transmit/Receive Switch Performance



Recommended PCB Configuration



Cross-Section View



The PCB dielectric between RF traces and RF ground layers should be chosen to reduce RF discontinuities between 50-Ω lines and package pins. M/A-COM recommends an FR-4 dielectric thickness of 0.008 in. (0.2 mm), yielding a 50-Ω line width of 0.015 in. (0.38 mm). The recommended metalization thickness is 1 oz. copper.

Shaded traces are vias to DC routing layer and traces on DC routing layer.

External Circuitry Parts List

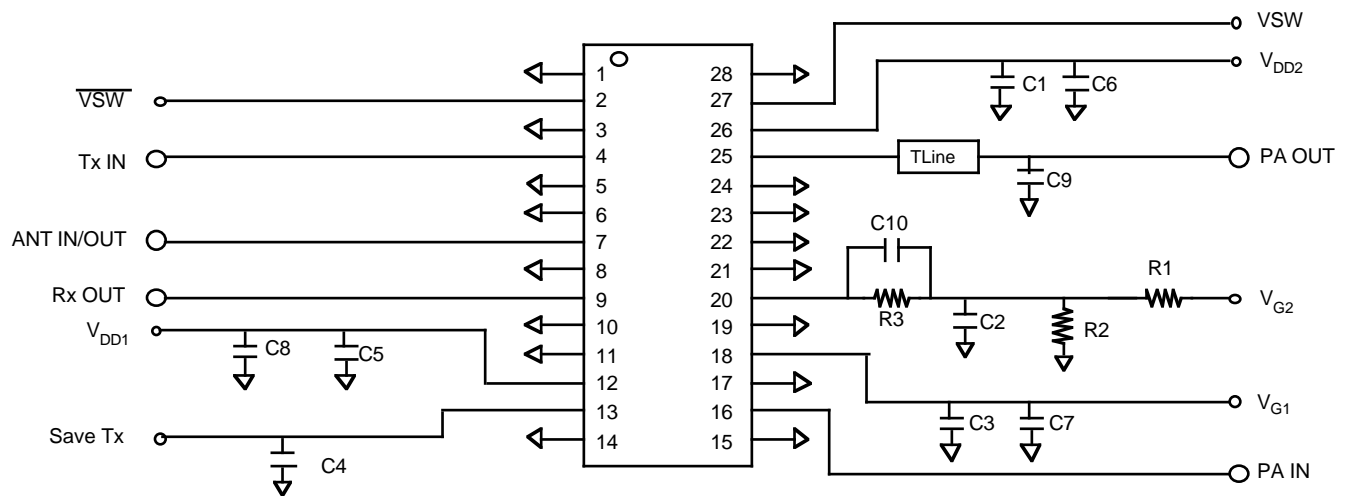
Label	Value	Purpose
C1 - C5	1000 pF	Low frequency bypass
C6 - C8	68 pF	RF bypass
C9	1.5 pF	Output power tuning
C10	15 pF	Reduces low frequency gain
R1	2.7 kΩ	Voltage divider to V_{G2}
R2	1.5 kΩ	Voltage divider to V_{G2}
R3	150 Ω	Reduces low frequency gain
Tline	0.250 in. long	Power match

Biasing Procedure

The AM55-0004 requires that V_{GG} bias be applied prior to **any** V_{DD} bias. Permanent damage may occur if this procedure is not followed. All FETs in the PA will draw excessive current and damage internal circuitry.

All off-chip components are low-cost surface mount components obtainable from multiple sources. (0.020 in. x 0.040 in. or 0.030 in. x 0.050 in.)

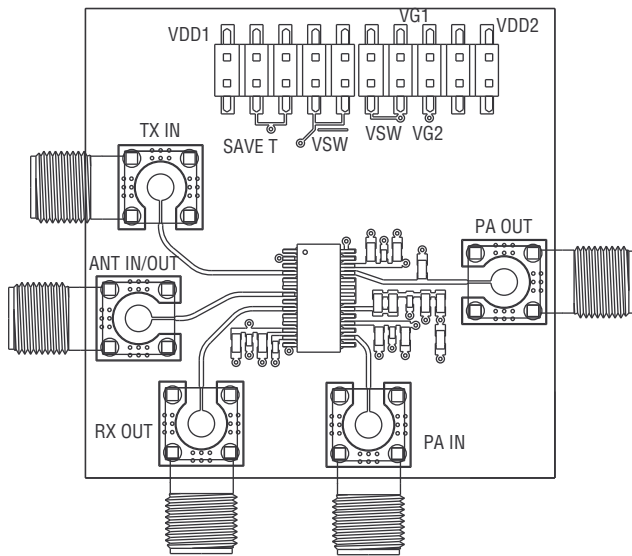
External Circuitry



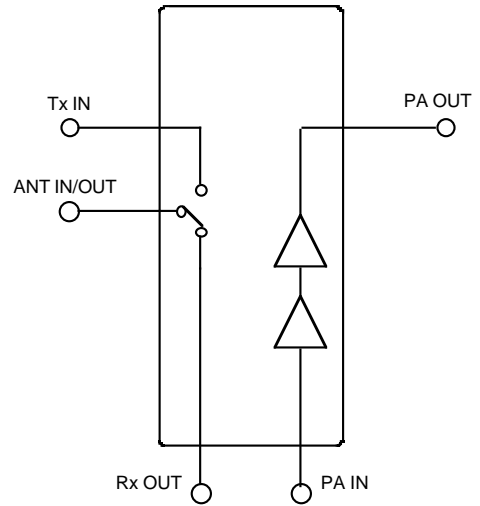
Designer's Kit (AM55-0004SMB)

The AM55-0004SMB Designer's Kit allows for immediate evaluation of M/A-COM's AM55-0004 integrated Power Amplifier and T/R Switch. The evaluation board consists of an AM55-0004, recommended external surface mount circuitry, RF connectors and a DC multipin connector, all mounted to a multi-layer FR-4 PCB. Other items included in the Designer's Kit: a floppy disk (with typical performance data and a .DXF file of the recommended PCB layout) and any additional Application Notes. The AM55-0004SMB PA/Switch evaluation PCB and block diagram are illustrated below with all functional ports labeled.

P/A Switch Sample Board



Functional Block Diagram



DC Connector Pinout

PCB DC Connector	Function	Device Pin Number
1	N/C	N/C
2	V _{DD1} (+ 4.8 V)	12
3	SAVE Tx (0 V/-4 V)	13
4	GND	N/C
5	SAVE Tx (0 V/-4 V)	13
6	V _{G1}	18
7	$\overline{\text{VSW}}$	2
8	GND	N/C
9	$\overline{\text{VSW}}$	2
10	V _{G1}	18

PCB DC Connector	Function	Device Pin Number
11	VSW	27
12	V _{G1}	18
13	VSW	27
14	GND	N/C
15	V _{G2}	20
16	V _{G1}	18
17	N/C	N/C
18	V _{G2}	20
19	N/C	N/C
20	V _{DD2} (+ 4.8 V)	26

AM55-0004SMB Biasing Procedure

In order to prevent transients which may damage the MMIC, please adhere to the following procedure.

- Turn on all power supplies and set all voltages to 0 volts BEFORE connecting the power supplies to the DC connector.
- Apply -4.0 volt supply or GND to DC connector pin 9 (\overline{VSW} , see truth table for desired mode).
- Apply -4.0 volt supply or GND to DC connector pin 13 (VSW, see truth table for desired mode).
- Apply a -4.0 volt supply to the DC connector pin 16 (V_{G1}).
- Apply a -4.0 volt supply to the DC connector pin 18 (V_{G2}).
- Apply a +4.8 volt supply to the DC connector pin 2 (V_{DD1}).
- Apply a +4.8 volt supply to the DC connector pin 20 (V_{DD2}).
- Apply GND to DC connector pin 5 (Save Tx).
- Adjust V_{G1} supply for desired V_{DD1} quiescent current (typically 30 mA).
- Adjust V_{G2} supply for desired V_{DD2} quiescent current (typically 65 mA).
- Change voltage on DC connector pin 5 as required (Save Tx, see truth table for desired mode).
- Apply RF power and test.
- To power off, reverse above procedure
 1. Set V_{G1} & V_{G2} to -4 V.
 2. Set V_{DD1} & V_{DD2} to 0 V.
 3. Set control voltage supplies to 0 V.
 4. Disconnect bias lines from DC connector.
 5. Turn off power supplies.

Evaluation PCB and RF Connector Losses

Port Reference	Estimated Loss (dB)
PA IN	0.15
PA OUT	0.20
Tx IN	0.20
ANT IN/OUT	0.20
Rx OUT	0.20

The DC connector on the Designer's Kit PCB allows selection of all the device's operating modes. It is accomplished by one or more of the following methods:

1. A mating female multi-pin connector (Newark Electronics Stock # 46F-4658, not included)
2. Wires soldered to the necessary pins (not included)
3. Clip leads (not included)
4. A combination of clip leads or wires and jumpers (jumpers included as required)